## Dual 2-to-4 Decoder/ Demultiplexer

The MC74VHCT139A is an advanced high speed CMOS 2–to–4 decoder/demultiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL devices while maintaining CMOS low power dissipation.

When the device is enabled ( $\overline{E} = low$ ), it can be used for gating or as a data input for demultiplexing operations. When the enable input is held high, all four outputs are fixed high, independent of other inputs.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device output is compatible with TTL-type input thresholds and the output has a full 5.0 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS logic, or from 1.8 V CMOS logic to 3.0 V CMOS logic while operating at the high-voltage power supply

The MC74VHCT139A input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the MC74VHCT139A to be used to interface 5.0 V circuits to 3.0 V circuits. The output structures also provide protection when  $V_{CC} = 0$  V. These input and output structures help prevent device destruction caused by supply voltage–input/output voltage mismatch, battery backup, hot insertion, etc.

#### Features

- High Speed:  $t_{PD} = 5.0 \text{ ns}$  (Typ) at  $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- TTL–Compatible Inputs:  $V_{IL} = 0.8 V$ ;  $V_{IH} = 2.0 V$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 V$  (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 100 FETs or 25 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



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		MARKING DIAGRAMS
1 1 1	SOIC-16 D SUFFIX CASE 751B	16 A A A A A A A A A A A A A A A A A A A
en frenteter 1	TSSOP-16 DT SUFFIX CASE 948F	16 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
G or ■	= Wafer L = Year N = Work W = Pb-Free	/eek

#### **FUNCTION TABLE**

	Inputs			Outputs			
Ē	A1	A0	YO	<u>Y1</u>	<u>Y2</u>	<u>Y3</u>	
н	X	Х	Н	Н	Н	Н	
L	L	L	L	Н	Н	Н	
L	L	н	н	L	Н	н	
L	Н	L	н	Н	L	Н	
L	н	Н	Н	Н	Н	L	

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.



En A0 A0 A1 Figure 3. Expanded Logic Diagram (1/2 of Device)



### MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	Digital Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage	Output in 3–State High or Low State	–0.5 to +7.0 –0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Diode Current		-20	mA
Ι <sub>ΟΚ</sub>	Output Diode Current		±20	mA
I <sub>OUT</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pi	ins	±75	mA
PD	Power Dissipation in Still Air	SOIC TSSOP	200 180	mW
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	>2000 >200 >2000	V
I <sub>LATCHUP</sub>	Latchup Performance	Above $V_{CC}$ and Below GND at 125°C (Note 4)	±300	mA
$\theta_{JA}$	Thermal Resistance, Junction-to-An	nbient SOIC TSSOP	143 164	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22-A114-A

2. Tested to EIA/JESD22-A115-A

3. Tested to JESD22-C101-A

4. Tested to EIA/JESD78

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	4.5	5.5	V
V <sub>IN</sub>	DC Input Voltage	0	5.5	V
V <sub>OUT</sub>	DC Output Voltage Output in 3–State High or Low State	0 0	5.5 V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, all Package Types	-55	125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0



Figure 6. Failure Rate vs. Time Junction Temperature

#### DC CHARACTERISTICS (Voltages Referenced to GND)

				Т	A = 25°	с	<b>T</b> <sub>A</sub> ≤	85°C		- 55 to 5°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		4.5 to 5.5	2			2		2		V
V <sub>IL</sub>	Maximum Low–Level Input Voltage		4.5 to 5.5			0.8		0.8		0.8	V
V <sub>OH</sub>	Maximum High–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu\text{A}$	4.5	4.4	4.5		4.4		4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -8 \text{ mA}$	4.5	3.94			3.8		3.66		
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	4.5		0	0.1		0.1		0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = 8 \text{ mA}$	4.5			0.36		0.44		0.52	
I <sub>IN</sub>	Input Leakage Current	$V_{IN} = 5.5 V \text{ or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μΑ
I <sub>CCT</sub>	Additional Quiescent Supply Current (per Pin)	Any one input: $V_{IN} = 3.4 V$ All other inputs: $V_{IN} = V_{CC}$ or GND	5.5			1.35		1.5		1.5	μΑ
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0			0.5		5		5	μΑ

#### AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns)

				1	「 <sub>A</sub> = 25°0	C	T <sub>A</sub> ≤	85°C	T <sub>A</sub> = - 125	- 55 to 5°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.2 9.7	11.0 14.5	1.0 1.0	13.0 16.5	1.0 1.0	13.0 16.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.0 6.5	7.2 9.2	1.0 1.0	8.5 10.5	1.0 1.0	8.5 10.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, $\overline{E}$ to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.4 8.9	9.2 12.7	1.0 1.0	11.0 14.5	1.0 1.0	11.0 14.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.4 5.9	6.3 8.3	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
C <sub>IN</sub>	Maximum Input Capacitance				4	10		10		10	pF
					Ţ	ypical @	25°C, V	<sub>CC</sub> = 5.0	V		
C <sub>PD</sub>	Power Dissipation Capac	itance (Note 5)		26				pF			

5.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/2$  (per decoder).  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .





Figure 7. Switching Waveform

Figure 8. Switching Waveform



\*Includes all probe and jig capacitance

Figure 9. Test Circuit

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHCT139ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74VHCT139ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74VHCT139ADTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74VHCT139ADTRG	TSSOP-16 (Pb-Free)	2500 Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## PACKAGE DIMENSIONS

SOIC-16 CASE 751B-05 ISSUE K



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	) BSC
J	0.19	0.25	0.008	0.009
Κ	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7 °
Ρ	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT



#### PACKAGE DIMENSIONS



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